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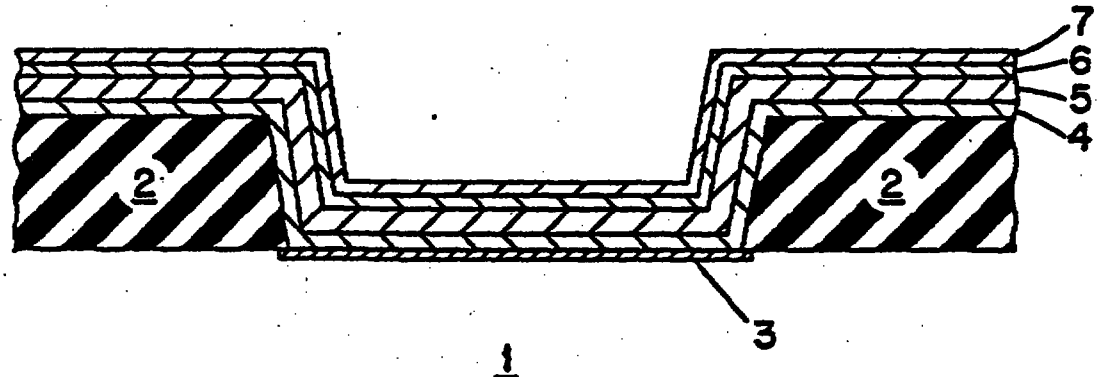
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(54) Title: ELECTROMIGRATION RESISTANT METALLIZATION STRUCTURES FOR MICROCIRCUIT INTERCONNECTIONS WITH RF-REACTIVELY SPUTTERED TITANIUM TUNGSTEN AND GOLD



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(57) Abstract

Two metallization schemes of PtSi/TiW/TiW(N)/Au (Type I) and PtSi/TiW/TiW(N)/TiW/Au (Type II) and associated process are described for microcircuit interconnections. The metallization schemes and process are capable of IC-interconnections with a metal-pitch as small as 1.5 μm, or even smaller. The metallization schemes are reliable for continuous high temperature and high current operations.

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